

AG 6A ... AG 6M



Silicon Rectifier Cells

with polysiloxan
passivation

AG 6A ... AG 6M

Forward Current: 6 A

Reverse Voltage: 50 to 1000 V

Publish Data

Features

Mechanical Data

- Weight approx. 0.3g
- ²⁾ $I_F = 6A$, $T_J = 25^\circ C$

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time $I_F = A$ $I_R = A$ $I_{RR} = A$ t_{rr} ns	Max. forward voltage $V_F^{2)}$
AG 6A	50	80		0,9
AG 6B	100	130		0,9
AG 6D	200	250		0,9
AG 6G	400	450		0,9
AG 6J	600	700		0,9
AG 6K	800	1000		0,9
AG 6M	1000	1300		0,9

Absolute Maximum Ratings

$T_C = 25^\circ C$ unless otherwise specified

Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 100^\circ C$ ¹⁾	6	A
I_{FRM}	Repetitive peak forward current $f > 15 Hz$ ¹⁾	40	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	400	A
i^2t	Rating for fusing, $t < 10 ms$ ³⁾	800	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾		K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾		K/W
T_J	Operating junction temperature	-50 ... +150°C	°C
T_s	Storage temperature	-50 ... +150°C	°C

Characteristics

$T_C = 25^\circ C$ unless otherwise specified

Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_J = 25^\circ C$; $V_R = V_{RRM}$	10	μA
	$T_J = 100^\circ C$; $V_R = V_{RRM}$	5	mA
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)		μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_J = ^\circ C$; inductive load switched off)		mJ

Dimensions in mm



